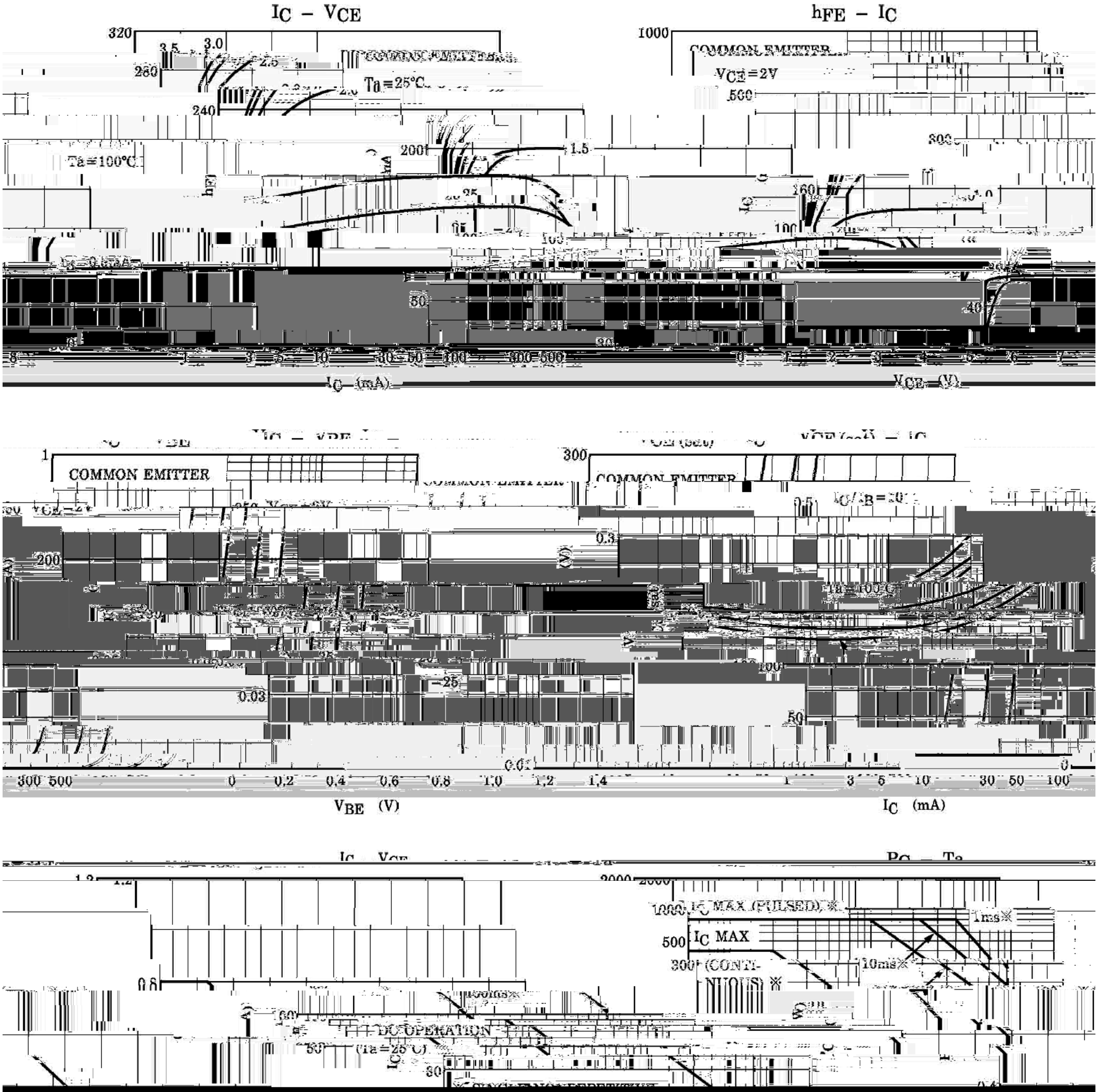
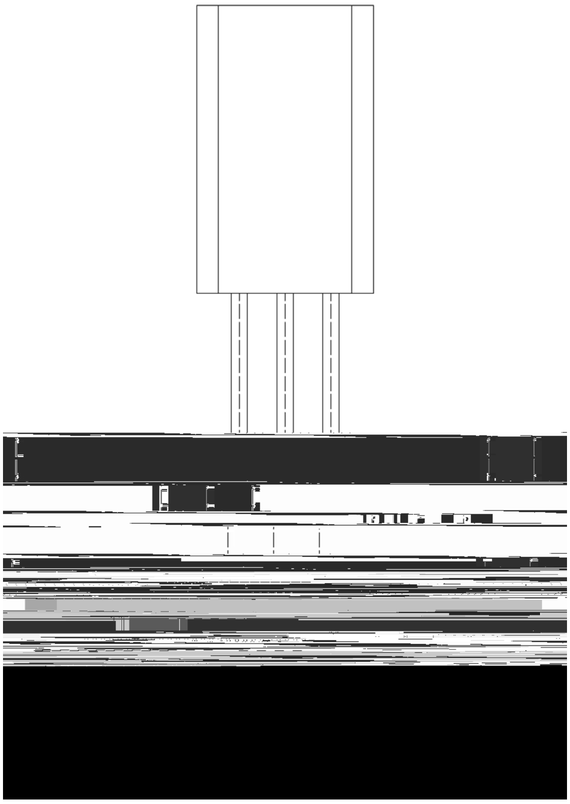
v ̏Ω Parameter	ɿ ᴺ Symbol	̏ΩӪ Rating	ᴅ Ꞝ Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	400	mA
Emitter Current – Continuous	I_E	-400	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̏Ω Parameter	ɿ ᴺ Symbol	╜ ׃ᛐ ƫ Test Conditions	ῳ ṇ Ӫ Min	Ɛ ʒ Ӫ Typ	ῳ ᶻ Ӫ Max	ᴅ Ꞝ Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=5.0mA I_B=0	80			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=2.0V I_C=50mA	70		240	
	$h_{FE(2)}$	V_{CE}=2.0V I_C=200mA	40			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=200mA I_B=20mA			0.4	V

/ Electrical Characteristic Curve



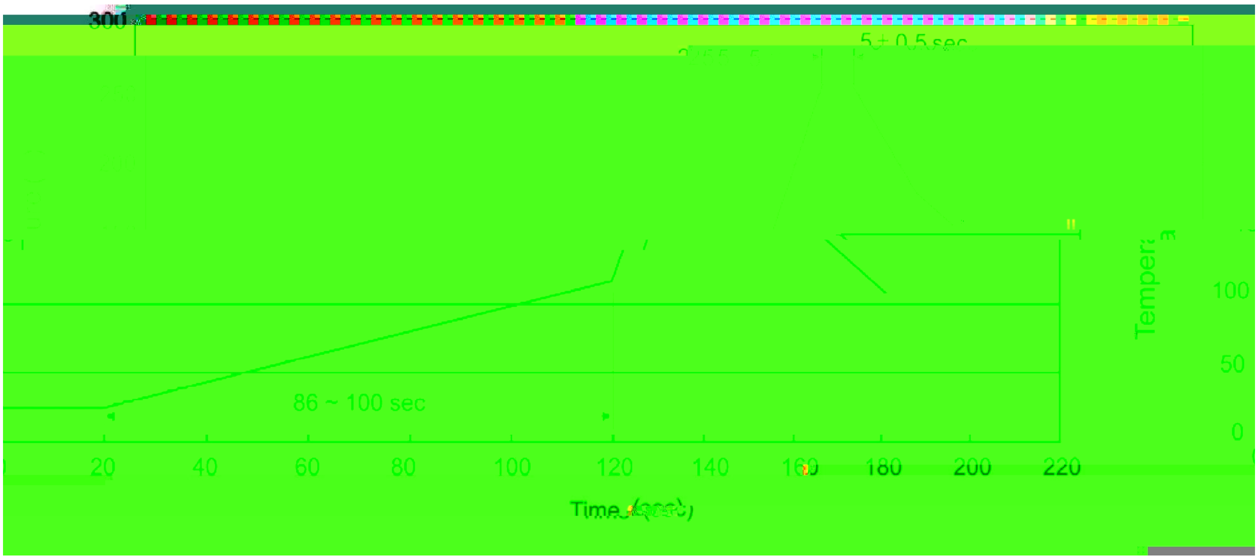
/ Marking Instructions



ب ˝ χ

EU:	Ѭ ʅ ᴎ Ђ
F495 : D χ	Ѭ ʓ ᴺ Ђ
R:	Ѭ k ɪʜ ˂ ⁶ Ђ

(　　) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ	Note:
1 ʅ ♬ □ ŷ 25 Ḱ 150 ɫ ı `H ڗ 60 Ḱ 90sec;	1.Preheating:25~150 ɫ , Time:60~90sec.
2 Ŝ Ӫ □ ŷ 255 ° 5 ɫ ı `H ڗ 'Y ᛀ ᚙ 5 ° 0.5sec;	2.Peak Temp.:255 ° 5 ɫ , Duration:5 ° 0.5sec.
3 ì ˙ ᛚ ˛ ɔ ⴰ ŷ ᚙ 2 Ḱ 10 ɫ /sec.	3. Cooling Speed: 2~10 ɫ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ŷ χ 270 ° 5 ɫ `H ڗ χ 10 ° ⅎ sec. Tf0.56D935.8(5(.7150)]TJ/TT7 1 Tf314.9486 0